

Features

Freq: 6~14GHz

Isolation: 20dB

Insertion Loss: 0.7dB

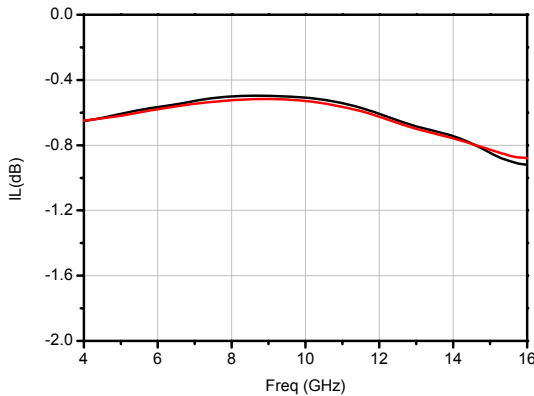
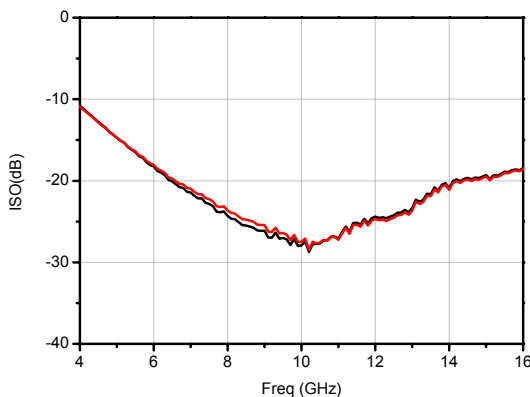
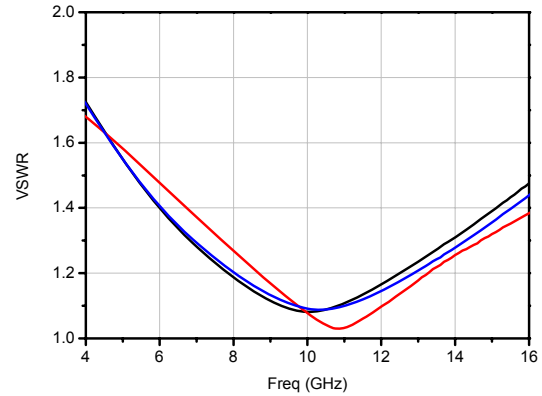
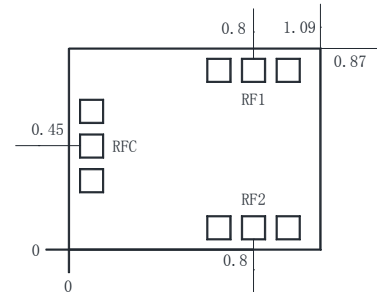
Chip Size: 1.09mm×0.87mm×0.1mm

General Description

The HG125GB-1 is a 2-way GaAs pHEMT power divider that is operating from 6 to 14 GHz. This chip features very high isolation of 20dB and extremely low insertion loss of 0.7dB. Input and output VSWR are 1.4/1.4.

Electrical Specifications ($T_A=25^\circ\text{C}$)

Parameter	Min.	Typ.	Max.
Frequency Range(GHz)	6~14		
Input VSWR	-	1.4	-
Output VSWR	-	1.4	-
Insertion Loss(dB)	-	0.7	-
Isolation (dB)	-	20	-

Insertion Loss

Isolation

Input and Output VSWR

Outline Drawing (mm)

Absolute Maximum Ratings

RF Input Power	+27dBm
Operating Temperature	-55°C~125°C
Storage Temperature	-65°C~150°C

Notes:

1. The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
2. GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
3. The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300°C, and no more than 30 sec.), and should make it fully grounded.
4. The chip microwave port and substrate gap is not exceeding 0.05mm, with $\Phi 25\mu\text{m}$ double gold wire bonding, suggested length of gold wire 250~400 μm .
5. Chip microwave port without DC blocking capacitor.
6. The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.